

Triacs

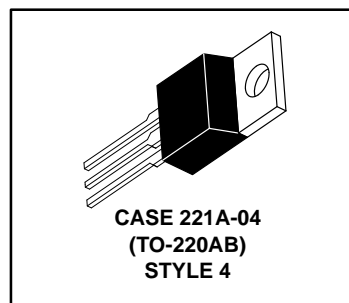
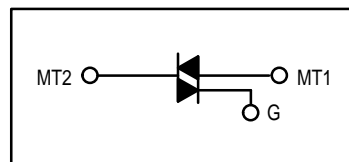
Silicon Bidirectional Thyristors

... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 800 Volts
- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- TO-220 Construction Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC218 Series) or Four Modes (MAC218A Series)

**MAC218
Series
MAC218A
Series**

**TRIACs
8 AMPERES RMS
200 thru 800 VOLTS**



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (Gate Open, $T_J = 25$ to 125°C)	V_{DRM}	200 400 600 800	Volts
On-State Current RMS (Conduction Angle = 360° , $T_C = +80^\circ\text{C}$)	$I_{\text{T(RMS)}}$	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, $T_C = 80^\circ\text{C}$, preceded and followed by rated current)	I_{TSM}	100	Amps
Fusing Current ($t = 8.3$ ms)	I^2t	40	A^2s
Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = $2 \mu\text{s}$)	P_{GM}	16	Watts
Average Gate Power ($T_C = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{\text{G(AV)}}$	0.35	Watt
Peak Gate Trigger Current (Pulse Width = $1 \mu\text{s}$)	I_{GTM}	4	Amps
Operating Junction Temperature Range	T_J	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

MAC218 Series MAC218A Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current ($V_D = \text{Rated } V_{DRM}$, gate open) $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I_{DRM}	— —	— —	10 2	μA mA
Peak On-State Voltage (Either Direction) ($I_{TM} = 11.3$ A Peak; Pulse Width = 1 to 2 ms, Duty Cycle < 2%)	V_{TM}	—	1.7	2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12$ Vdc, $R_L = 12\Omega$) Trigger Mode MT2(+), Gate(+); MT2(+), Gate(-); MT2(-), Gate(-) MT2(-), Gate(+) "A" SUFFIX ONLY	I_{GT}	— —	— —	50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY (Main Terminal Voltage = Rated V_{DRM} , $R_L = 10$ k Ω , $T_J = +125^{\circ}C$) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY	V_{GT}	— — — — 0.2 0.2	0.9 0.9 1.1 1.4 — —	2 2 2 2.5 — —	Volts
Holding Current (Either Direction) ($V_D = 24$ Vdc, Gate Open, Initiating Current = 200 mA)	I_H	—	—	50	mA
Critical Rate of Rise of Commutating Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11.3$ A, Commutating $di/dt = 4.1$ A/ms, Gate Unenergized, $T_C = 80^{\circ}C$)	$dv/dt(c)$	—	5	—	V/ μs
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Voltage Rise, Gate Open, $T_J = 125^{\circ}C$)	dv/dt	—	100	—	V/ μs

FIGURE 1 — CURRENT DERATING

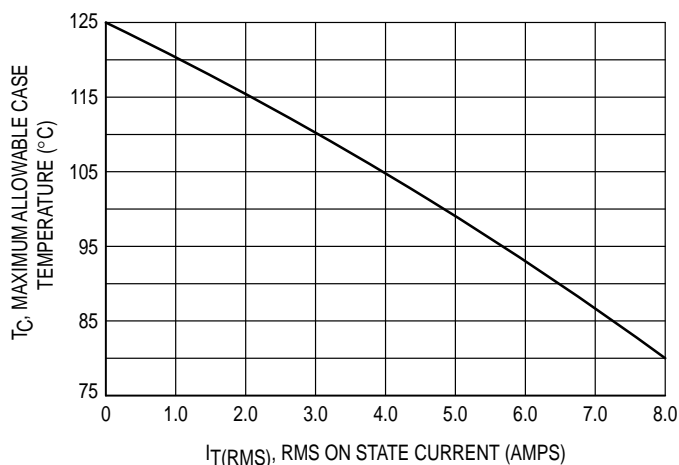


FIGURE 2 — POWER DISSIPATION

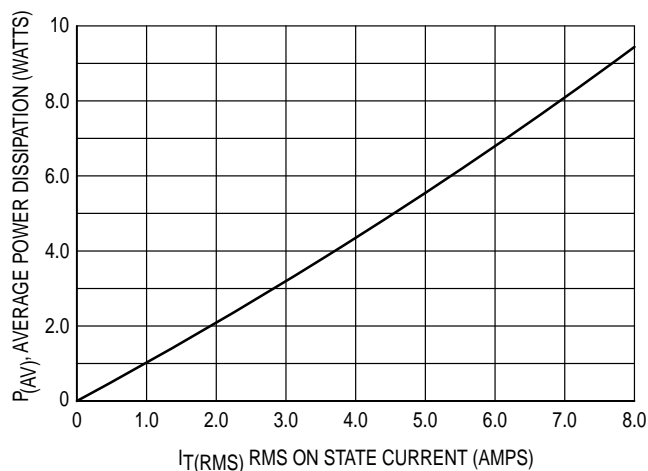


FIGURE 3 — NORMALIZED GATE TRIGGER CURRENT

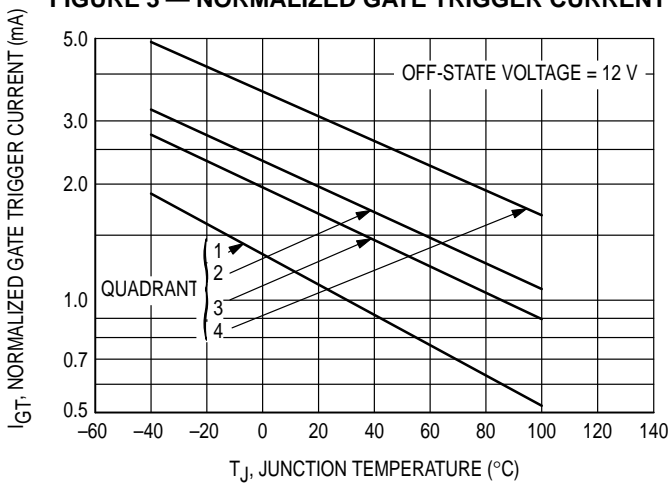


FIGURE 4 — NORMALIZED GATE TRIGGER VOLTAGE

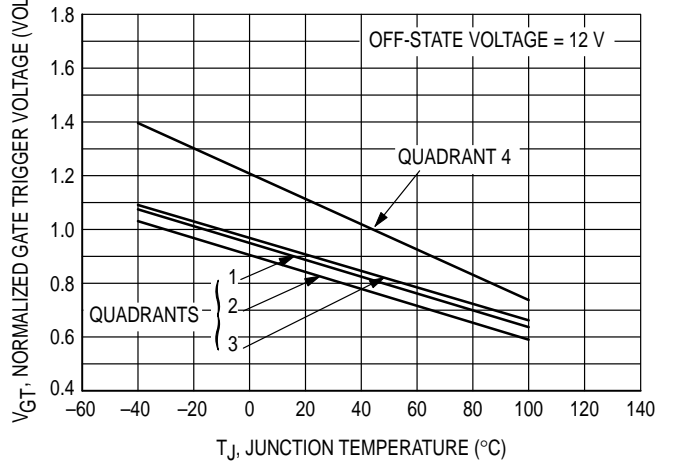
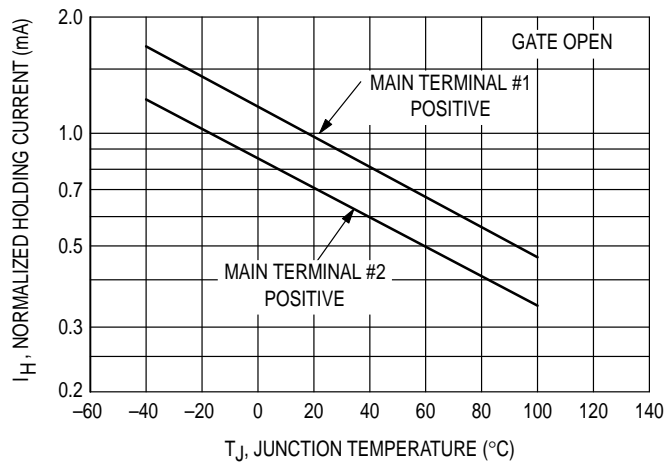
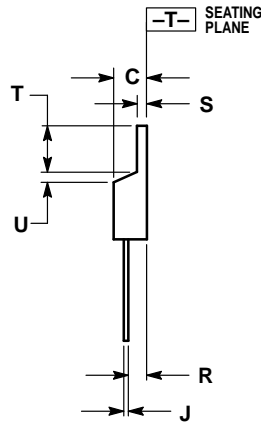
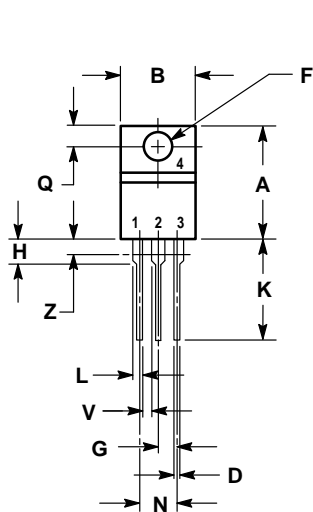


FIGURE 5 — NORMALIZED HOLDING CURRENT



PACKAGE DIMENSIONS



STYLE 4:
 PIN 1. MAIN TERMINAL 1
 2. MAIN TERMINAL 2
 3. GATE
 4. MAIN TERMINAL 2

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

CASE 221A-04
(TO-220AB)

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